









# **B2D10065F**

#### 650V ▲ 10A ▲ SiC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ SMD type

Excellent surge capability

Easy paralleling due to positive V<sub>F</sub> temperature coefficient

TO-263-2L (D2PAK) package ▲ Epoxy meets UL94-V0 ▲ MSL3

Temperature independent switching

Ultra-low forward voltage and high surge current

#### **SPECIFICATION**

Item (T <sub>c</sub> = 25°C, unless otherwise noted)		Characteristics
Operating Temperature Range	Tj	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	$V_{RRM}$	650V
Continuous Forward Current at T <sub>c</sub> = 155°C	I <sub>F</sub>	10A
Total Capacitive Charge (T <sub>J</sub> = 25°C)	$\mathbf{Q}_{C}$	29nC
Capacitance Stored Energy (V <sub>R</sub> = 400V)	Ec	7.5µJ
Diode Forward Voltage (T <sub>J</sub> = 175°C, I <sub>F</sub> = 10A)		1.67V
Power Dissipation	P <sub>TOT</sub>	125W

#### **APPLICATIONS**

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
<b>₹</b> /•			PFC	*		

#### **PIN DESCRIPTION**

Circuit Diagram	Outline • Top View	Pin No.	Description
Case 0 1 2	Case 1 2	1 2	Cathode (Case Backside) Anode

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## ABSOLUT MAXIMUM RATINGS ▲ T<sub>C</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		$V_{RRM}$	650	V
Non-Repetitive Peak Reverse Voltage		$V_{RSM}$	650	V
Continuous Forward Current	T <sub>C</sub> = 25°C	I <sub>F</sub>	34	Α
Continuous Forward Current	$T_C = 155^{\circ}C$	I <sub>F</sub>	10	Α
Non-Repetitive Forward Surge Current	$T_C$ = 25°C, $t_p$ = 10ms, Half Sine Wave	I <sub>FSM</sub>	75	Α
I <sup>2</sup> t Value	$T_C = 25^{\circ}C$ , $t_p = 10$ ms	∫i²dt	28.12	$A^2s$
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>TOT</sub>	125	W
Power Dissipation	T <sub>C</sub> = 110°C	$P_{TOT}$	54	W
Operating Junction Temperature		T <sub>J</sub>	-55 to +175	°C
Storage Temperature Range		$T_{STG}$	-55 to +175	°C

## **ELECTRICAL CHARACTERISTICS**

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T <sub>J</sub> = 25°C	$V_{DC}$	650			V
Diode Forward Voltage	$I_F = 10A, T_J = 25^{\circ}C$	$V_{F}$		1.29		V
Diode Forward Voltage	$I_F = 10A, T_J = 175$ °C	$V_{F}$		1.67		V
Reverse Current	$V_R = 650V, T_J = 25^{\circ}C$	$I_R$		2		μΑ
Reverse Current	$V_R = 650V$ , $T_J = 175$ °C	$I_R$		20		μΑ
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
	$V_R = 400V, T_J = 25^{\circ}C$					
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$	Qc		29		nC
Total Capacitance	$V_R = 1V$ , $f = 1MHz$ , $T_J = 25$ °C	С		457		pF
Total Capacitance	$V_R = 300V$ , $f = 1MHz$ , $T_J = 25$ °C	С		49.7		pF
Total Capacitance	$V_R$ = 600V, f = 1MHz, $T_J$ = 25°C	С		49.3		pF
Capacitance Stored Energy	$V_R = 400V, T_J = 25^{\circ}C$	E <sub>C</sub>		7.5		μJ

#### THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		1.192		K/W



#### REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 1 - Typical Forward Characteristics I<sub>F</sub> vs. V<sub>F</sub>

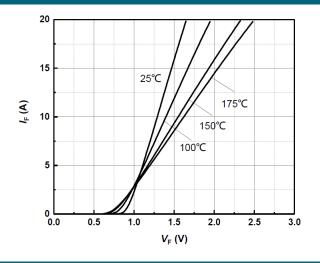


Fig. 2 • Typical Reverse Current I<sub>R</sub> as function of Reverse Voltage V<sub>R</sub>

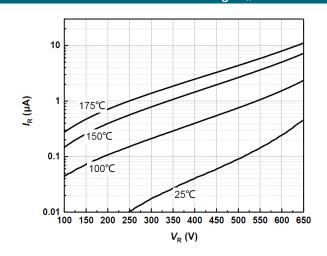


Fig. 3 • Diode Forward Current  $I_F$  as function of Case Temperature  $T_C$  (D = Duty Cycle)

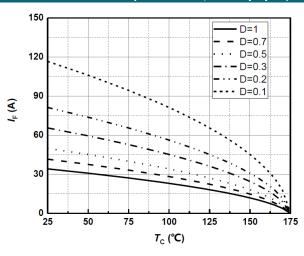


Fig. 4 • Typical Capacitance C as function of Reverse Voltage  $V_R$ ,  $C = f(V_R)$ ,  $T_J = 25^{\circ}C$ , f = 1MHz

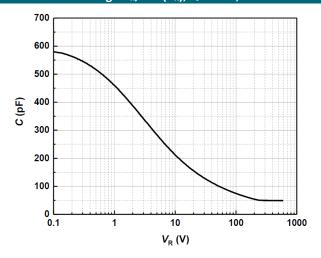


Fig. 5 • Typical Reverse Charge Q<sub>C</sub> as function of Reverse Voltage V<sub>R</sub>

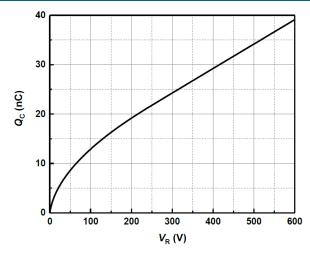
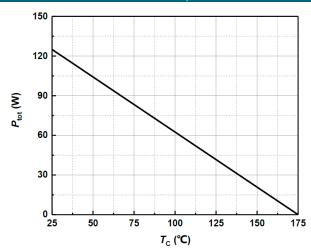


Fig. 6 • Power Dissipation  $P_{\text{TOT}}$  as function of Case Temperature  $T_c$ 



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#### REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 7 - Capacitance Stored Energy

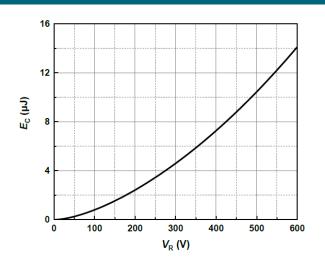
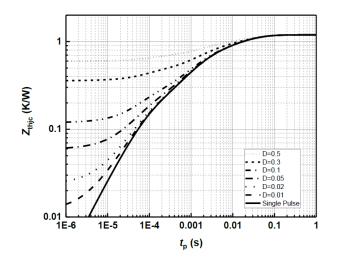
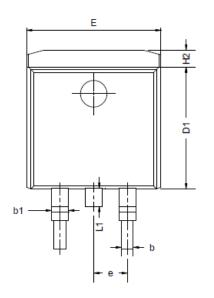


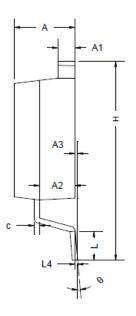
Fig. 8 • Maximum Transient Thermal Impedance, Z<sub>thjc</sub> = f(t), Parameter: D = t/T

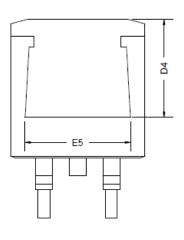


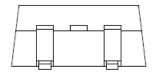


## **PACKAGE OUTLINE**









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
С	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	_	_

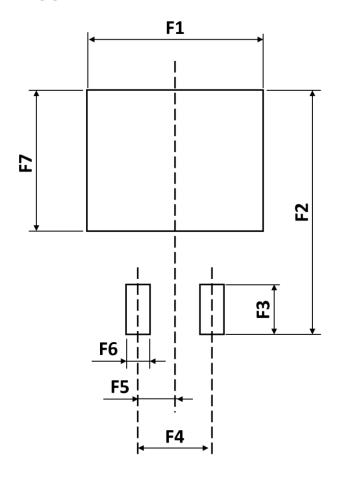
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Е	9.86	10.16	10.36
E5	7.06	-	-
е		2.54 BSC	
Н	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4		0.25 BSC	
$\theta$	0°	5°	9°

## **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
B2D10065F	TO-263-2L (D2PAK)	Reel	800pcs	4,000pcs	4,000pcs



#### **RECOMMENDED PAD LAYOUT**



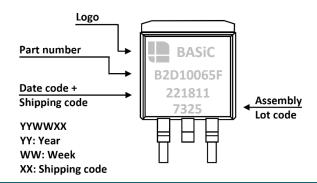
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-
F2	-	- 16.90	
F3	-	2.54	-
F4	-	5.08	-

Sym	Millimeters (Min.)	Millimeters (Max.)	
F5	-	2.54	-
F6	-	1.60	-
F7	-	9.75	-

#### **Notes:**

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

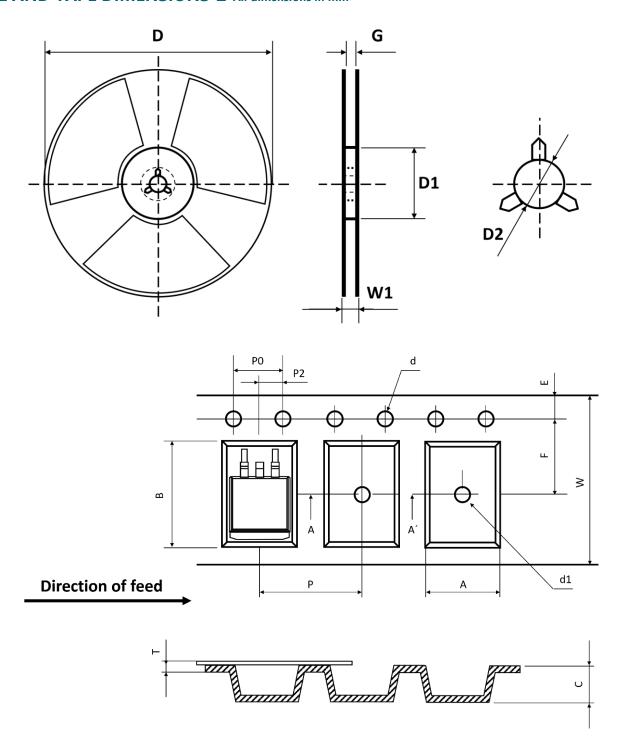
#### **PART MARKING**



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#### REEL AND TAPE DIMENSIONS A All dimensions in mm

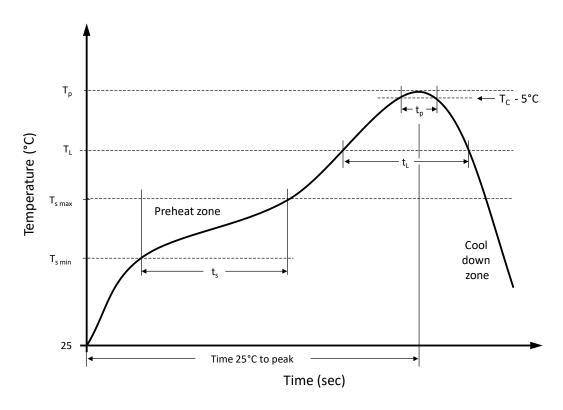


Package	W	Α	В	С	d1	D	Ε	F	Р	P0	T	D	D1	D2	G	W1
TO263-2L	24.00	10.70	16.30	5.10	1.50	1.50	1.75	11.50	16.00	4.00	0.35	330	50	13.00	24.40	30.40
10263-2L	±0.30	±0.10	±0.10	±0.10	Max.	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.30	Min.	±0.50	Min.	Min.

Note: All dimensions meet EIA-481-D requirements.



## RECOMMENDED REFLOW SOLDERING PROFILE



## **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T <sub>s max</sub>	150 °C	200 °C
Preheat time t <sub>s</sub> from T <sub>s min</sub> to T <sub>s max</sub>	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	$T_L$	183 °C	217 °C
Time t <sub>L</sub> maintained above T <sub>L</sub>	t <sub>L</sub>	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate (T <sub>L</sub> to T <sub>p</sub> )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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